Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) Semiconductor-on-insulator substrate successively comprising a base ~~(1)~~, a diamond-like carbon layer ~~(3)~~, a layer made of dielectric material ~~(4)~~ and a layer made of semi-conducting material ~~(5)~~ designed to constitute microelectronic elements, the dielectric material ~~(4)~~ being chosen such that the upper level ~~(Edi)~~ of the valence band of the dielectric material ~~(4)~~ is lower than the upper level ~~(Ecd)~~ of the valence band of the diamond-like carbon ~~(3)~~ and the semi-conducting material ~~(5)~~ being chosen such that the upper level ~~(Esc)~~ of the valence band of the semi-conducting material ~~(5)~~ is higher than the upper level ~~(Ecd)~~ of the valence band of the diamond-like carbon ~~(3)~~, substrate characterized in that it comprises an alumina nucleation layer ~~(2)~~ disposed between the base ~~(1)~~ and the diamond-like carbon layer ~~(3)~~.

2. (Currently Amended) Substrate according to claim 1, ~~characterized in that~~ wherein the semi-conducting material ~~(5)~~ is chosen from silicon, germanium and indium antimonide.

3. (Currently Amended) Substrate according to ~~one of the claims 1 and 2, characterized in that~~ claim 1, wherein the dielectric material ~~(4)~~ is chosen from alumina ~~(Al2O2)~~, hafnium oxide ~~(Hf02)~~ and zirconium oxide ~~(ZrO2)~~.

4. (Currently Amended) Substrate according to claim 3, ~~characterized in that~~ wherein the dielectric material layer is made of monocrystalline alumina.

5. (Currently Amended) Substrate according to ~~any one of the claims 1 to 4, characterized in that~~ claim 1, wherein the nucleation layer ~~(2)~~ is made of monocrystalline alumina.

6. (Currently Amended) Substrate according to ~~any one of the claims 1 to 5, characterized in that~~ claim 1, wherein the dielectric material layer ~~(4)~~ is formed by superposition of two dielectric layers.

7. (Currently Amended) Method for making a substrate according to ~~any one of the claims 1 to 6, characterized in that comprises~~ claim 1, comprising preparation of a first stack ~~(11)~~ by:

deposition of the diamond-like carbon layer ~~(3)~~ on the base ~~(1)~~, and

deposition of the dielectric material layer ~~(4)~~ on the diamond-like carbon layer ~~(3)~~.

8. (Currently Amended) Method according to claim 7, ~~characterized in that it comprises~~comprising deposition of the nucleation layer ~~(2)~~ on the base ~~(1)~~, before deposition of the diamond-like carbon layer ~~(3)~~.

9. (Currently Amended) Method according to ~~one of the claims 7 and 8, characterized in that it comprises~~ claim 7, comprising deposition of the semi-conducting material ~~(5)~~ designed to constitute microelectronic elements, after deposition of the dielectric material layer ~~(4)~~.

10. (Currently Amended) Method according to ~~any one of the claims 7 and 8, characterized in that it comprises~~claim 7, comprising preparation of a second stack ~~(12)~~ by:

deposition of a first additional dielectric layer ~~(14)~~ on an additional base ~~(13)~~,

deposition of the semi-conducting ~~(5)~~ material designed to constitute microelectronic elements, on the first additional dielectric layer ~~(14)~~, and

deposition of a second additional dielectric layer ~~(15)~~ on the semi-conducting material ~~(5)~~, and

after preparation of the first ~~(11)~~ and second ~~(12)~~ stacks, assembly of the first ~~(11)~~ and second ~~(12)~~ stacks by molecular bonding of the second additional dielectric layer

~~(15)~~ and of the dielectric material layer ~~(4)~~, the additional base ~~(13)~~ then being removed by etching.

11. (Currently Amended) Method according to claim 10, ~~characterized in that it comprises~~ comprising removal of the first additional dielectric layer ~~(14)~~.

12. (Currently Amended) Method according to ~~one of the claims 7 and 8, characterized in that,~~claim 7, wherein, a second stack ~~(12)~~ being formed by an additional substrate comprising a thin film ~~(18)~~ of the semi-conducting material ~~(5)~~ designed to constitute microelectronic elements, the thin film ~~(18)~~ being delineated by a buried zone ~~(19)~~ fragilized by implantation, the first ~~(11)~~ and second ~~(12)~~ stacks are assembled by molecular bonding of the thin film ~~(18)~~ and of the dielectric material layer ~~(4)~~, the second stack ~~(12)~~ being dissociated, after bonding, at the level of the fragilized buried zone ~~(19)~~.

13. (Currently Amended) Method according to claim 12, ~~characterized in that it comprises~~comprising thermal oxidation of the thin film ~~(18)~~, before assembly, so as to form a thermal oxide layer ~~(20)~~.